

PU3119, PU4119, PU4419

Package Dimensions

Silicon NPN Triple-Diffused Planar Type

Power Amplifier, Switching

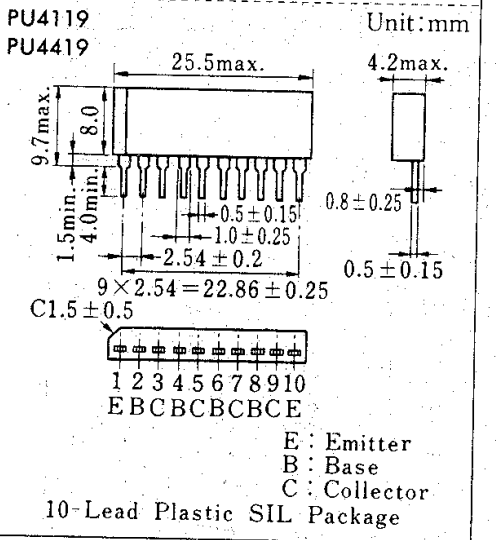
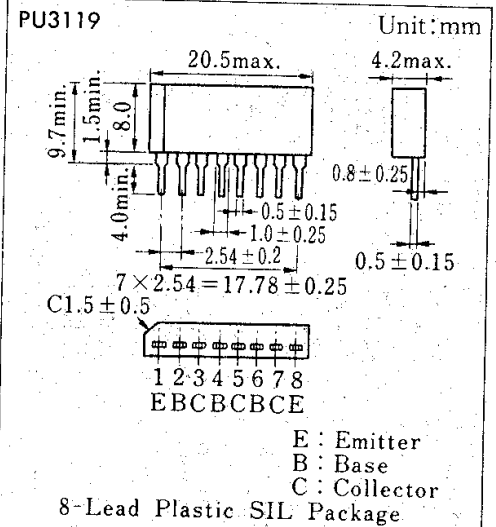
Complementary Pair with PU3219, PU4219, PU4519

Features

- High DC current gain (h_{FE})
- Good linearity of DC current gain (h_{FE})
- PU3119: 3 NPN elements
- PU4119: 4 NPN elements
- PU4419: 2 NPN elements \times 2 (4 elements in total)

Absolute Maximum Ratings ($T_c=25^\circ\text{C}$)

Item	Symbol	Value	Unit
Collector-base voltage	V_{CBO}	60	V
Collector-emitter voltage	V_{CEO}	60	V
Emitter-base voltage	V_{EBO}	5	V
Peak collector current	I_{CP}	4	A
Collector current	I_C	2	A
Power dissipation	P_D	15	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{str}	-55 ~ +150	$^\circ\text{C}$



Electrical Characteristics ($T_c=25^\circ\text{C}$)

Item	Symbol	Condition				Unit
			min.	typ.	max.	
Collector cutoff current	I_{CBO}	$V_{CB}=60\text{V}, I_E=0$			1	mA
	I_{CEO}	$V_{CE}=30\text{V}, I_B=0$			2	mA
Emitter cutoff current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$			2	mA
Collector-emitter voltage	V_{CEO}	$I_C=30\text{mA}, I_B=0$	60			V
DC current gain	h_{FE1}	$V_{CE}=4\text{V}, I_C=1\text{A}$	1000			
	h_{FE2}^*	$V_{CE}=4\text{V}, I_C=2\text{A}$	1000		10000	
Base-emitter voltage	V_{BE}	$V_{CE}=4\text{V}, I_C=2\text{A}$			2.8	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=2\text{A}, I_B=8\text{mA}$			2.5	V
Transition frequency	f_T	$V_{CE}=10\text{V}, I_C=0.5\text{A}, f=1\text{MHz}$		20		MHz
Turn-on time	t_{on}	$I_C=2\text{A}, I_{B1}=8\text{mA}, I_{B2}=-8\text{mA}$		0.5		μs
Storage time	t_{str}			4		μs
Fall time	t_f			1		μs

E2 Classifications

Class	Free	Q*	P
E2	1000 ~ 10000	1000 ~ 5000	2000 ~ 10000